

High Speed Optocoupler, 100 kBd, Low Input Current, Photodiode Darlington Output

Features

- High Current Transfer Ratio, 300 %
 - Low Input Current, 0.5 mA
 - High Output Current, 60 mA
 - Isolation Test Voltage, 5300 V_{RMS}
 - TTL Compatible Output, V_{OL} = 0.1 V
 - High Common Mode Rejection, 500 V/μs
 - Adjustable Bandwidth-Access to Base
 - Standard Molded Dip Plastic Package
 - Lead-free component
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- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

Agency Approvals

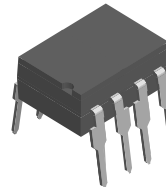
- UL1577, File No. E52744 System Code H or J, Double Protection
- DIN EN 60747-5-2 (VDE0884)
DIN EN 60747-5-5 pending
Available with Option 1

Applications

Logic Ground Isolation-TTL/TTL, TTL/CMOS, CMOS/CMOS, CMOS/TTL
 EIA RS 232 Line Receiver
 Low Input Current Line Receiver-Long Lines, Party Lines
 Telephone Ring Detector
 117 VAC Line Voltage Status Indication-Low Input Power Dissipation
 Low Power Systems-Ground Isolation

Description

High common mode transient immunity and very high current ratio together with 5300 V_{RMS} insulation are achieved by coupling an LED with an integrated high gain photo detector in an eight pin dual-in-line package. Separate pins for the photo diode and output stage enable TTL compatible saturation voltages with high speed operation.



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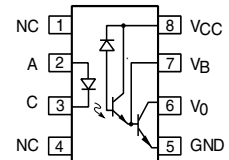


Photo darlington operation is achieved by tying the V_{CC} and V_O terminals together. Access to the base terminal allows adjustment to the gain bandwidth.

The 6N138 is ideal for TTL applications since the 300 % minimum current transfer ratio with an LED current of 1.6 mA enables operation with one unit load-in and one unit load-out with a 2.2 kΩ pull-up resistor.

The 6N139 is best suited for low power logic applications involving CMOS and low power TTL. A 400 % current transfer ratio with only 0.5 mA of LED current is guaranteed from 0 °C to 70 °C

Caution: Due to the small geometries of this device, it should be handled with Electrostatic Discharge (ESD) precautions. Proper grounding would prevent damage further and/or degradation which may be induced by ESD.

Order Information

| Part | Remarks |
|------------|-------------------------------|
| 6N138 | CTR > 300 %, DIP-8 |
| 6N139 | CTR > 500 %, DIP-8 |
| 6N138-X007 | CTR > 300 %, SMD-8 (option 7) |
| 6N138-X009 | CTR > 300 %, SMD-8 (option 9) |
| 6N139-X007 | CTR > 500 %, SMD-8 (option 7) |
| 6N139-X009 | CTR > 500 %, SMD-8 (option 9) |

For additional information on the available options refer to Option Information.

Absolute Maximum Ratings

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Stresses in excess of the absolute Maximum Ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute Maximum Rating for extended periods of the time can adversely affect reliability.

Input

| Parameter | Test condition | Symbol | Value | Unit |
|---|----------------|--------------|-------|------|
| Reverse voltage | | V_R | 5.0 | V |
| Forward current | | I_F | 25 | mA |
| Average input current | | $I_{F(AVG)}$ | 20 | mA |
| Input power dissipation ^{1), 3)} | | P_{diss} | 35 | mW |

Output

| Parameter | Test condition | Part | Symbol | Value | Unit |
|--|---|-------|---------------|--------------|------|
| Supply and output voltage | pin 8-5, pin 6-5 | 6N138 | V_{CC}, V_O | - 0.5 to 7.0 | V |
| | pin8-5, pin 6-5 | 6N139 | V_{CC}, V_O | - 0.5 to 18 | V |
| Emitter base reverse voltage | pin 5-7 | | | 0.5 | V |
| Peak input current | 50 % duty cycle - 1.0 ms pulse width | | | 40 | mA |
| Peak transient input current | $t_p \leq 1.0\text{ }\mu\text{s}$, 300 pps | | | 1.0 | A |
| Output current | pin 6 | | I_O | 60 | mA |
| Output power dissipation ^{2), 4)} | | | P_{diss} | 100 | mW |

Coupler

| Parameter | Test condition | Symbol | Value | Unit |
|----------------------------|---|-----------|----------------|--------------------|
| Isolation test voltage | | V_{ISO} | 5300 | V_{RMS} |
| Isolation resistance | $V_{IO} = 500\text{ V}$, $T_{amb} = 25\text{ }^{\circ}\text{C}$ | R_{IO} | $\geq 10^{12}$ | Ω |
| | $V_{IO} = 500\text{ V}$, $T_{amb} = 100\text{ }^{\circ}\text{C}$ | R_{IO} | $\geq 10^{11}$ | Ω |
| Storage temperature | | T_{stg} | - 55 to + 125 | $^{\circ}\text{C}$ |
| Operating temperature | | T_{amb} | - 55 to + 100 | $^{\circ}\text{C}$ |
| Lead soldering temperature | $t = 10\text{ s}$ | T_{sld} | 260 | $^{\circ}\text{C}$ |

¹⁾ Derate linearly above 50 $^{\circ}\text{C}$ free-air temperature at a rate of 0.4 mA/ $^{\circ}\text{C}$

²⁾ Derate linearly above 50 $^{\circ}\text{C}$ free-air temperature at a rate of 0.7 mW/ $^{\circ}\text{C}$

³⁾ Derate linearly above 25 $^{\circ}\text{C}$ free-air temperature at a rate of 0.7 mA/ $^{\circ}\text{C}$

⁴⁾ Derate linearly above 25 $^{\circ}\text{C}$ free-air temperature at a rate of 2.0 mW/ $^{\circ}\text{C}$

Electrical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.

Input

| Parameter | Test condition | Symbol | Min | Typ. | Max | Unit |
|--|-------------------------------|--------|-----|-------|-----|------------------------|
| Input forward voltage | $I_F = 1.6\text{ mA}$ | V_F | | 1.4 | 1.7 | V |
| Input reverse breakdown voltage | $I_R = 10\text{ }\mu\text{A}$ | BV_R | 5.0 | | | V |
| Temperature coefficient of forward voltage | $I_F = 1.6\text{ mA}$ | | | - 1.8 | | mV/ $^{\circ}\text{C}$ |

Output

| Parameter | Test condition | Part | Symbol | Min | Typ. | Max | Unit |
|--|--|-------|-----------|-----|-------|-----|---------------|
| Logic low, output voltage ⁶⁾ | $I_F = 1.6\text{ mA}$, $I_O = 4.8\text{ mA}$, $V_{CC} = 4.5\text{ V}$ | 6N138 | V_{OL} | | 0.1 | 0.4 | V |
| | $I_F = 1.6\text{ mA}$, $I_O = 8.0\text{ mA}$, $V_{CC} = 4.5\text{ V}$ | 6N139 | V_{OL} | | 0.1 | 0.4 | V |
| | $I_F = 5.0\text{ mA}$, $I_O = 15\text{ mA}$, $V_{CC} = 4.5\text{ V}$ | 6N139 | V_{OL} | | 0.15 | 0.4 | V |
| | $I_F = 12\text{ mA}$, $I_O = 24\text{ mA}$, $V_{CC} = 4.5\text{ V}$ | 6N139 | V_{OL} | | 0.25 | 0.4 | V |
| Logic high, output current ⁶⁾ | $I_F = 0\text{ mA}$, $V_{CC} = V_{CC} = 7.0\text{ V}$ | 6N138 | I_{OH} | | 0.1 | 250 | μA |
| | $I_F = 0\text{ mA}$, $V_{CC} = V_{CC} = 18\text{ V}$ | 6N139 | I_{OH} | | 0.05 | 100 | μA |
| Logic low supply current ⁶⁾ | $I_F = 1.6\text{ mA}$, $V_O = \text{OPEN}$, $V_{CC} = 18\text{ V}$ | | I_{CCL} | | 0.2 | 1.5 | mA |
| Logic high supply current ⁶⁾ | $I_F = 0\text{ mA}$, $V_O = \text{OPEN}$, $V_{CC} = 18\text{ V}$ | | I_{CCH} | | 0.001 | 10 | μA |

⁶⁾ Pin 7 open

Coupler

| Parameter | Test condition | Symbol | Min | Typ. | Max | Unit |
|---|--|----------|-----|-----------|-----|---------------|
| Input capacitance | $f = 1.0\text{ MHz}$, $V_F = 0$ | C_{IN} | | 25 | | pF |
| Input output insulation leakage current ⁷⁾ | 45 % relative humidity, $T_{amb} = 25\text{ }^{\circ}\text{C}$, $t = 5.0\text{ s}$, $V_{IO} = 3000\text{ VDC}$ | | | | 1.0 | μA |
| Resistance (input output) ⁷⁾ | $V_{IO} = 500\text{ VDC}$ | R_{IO} | | 10^{12} | | Ω |
| Capacitance (input-output) ⁷⁾ | $f = 1.0\text{ MHz}$ | C_{IO} | | 0.6 | | pF |

⁷⁾ Device considered a two-terminal device: pins 1, 2, 3 and 4 shorted together and pins 5, 6, 7, and 8 shorted together.

Current Transfer Ratio

| Parameter | Test condition | Part | Symbol | Min | Typ. | Max | Unit |
|--|--|-------|--------|-----|------|-----|------|
| Current Transfer Ratio ^{5), 6)} | $I_F = 1.6 \text{ mA}$, $V_O = 0.4 \text{ V}$, $V_{CC} = 4.5 \text{ V}$ | 6N138 | CTR | 300 | 1600 | | % |
| Current Transfer Ratio | $I_F = 0.5 \text{ mA}$, $V_O = 0.4 \text{ V}$, $V_{CC} = 4.5 \text{ V}$ | 6N139 | CTR | 400 | 1600 | | % |
| | $I_F = 1.6 \text{ mA}$, $V_O = 0.4 \text{ V}$, $V_{CC} = 4.5 \text{ V}$ | 6N139 | CTR | 500 | 2000 | | % |

⁵⁾ DC current transfer ratio is defined as the ratio of output collector current, I_O , to the forward LED input current, I_F times 100 %.

⁶⁾ Pin 7 open

Switching Characteristics

| Parameter | Test condition | Part | Symbol | Min | Typ. | Max | Unit |
|--|--|-------|-----------|-----|------|-----|---------------|
| Propagation delay time to logic low at output | $I_F = 1.6 \text{ mA}$, $R_L = 2.2 \text{ k}\Omega$ | 6N138 | t_{PHL} | | 2.0 | 10 | μs |
| Propagation delay time to logic low at output ^{6), 8)} | $I_F = 0.5 \text{ mA}$, $R_L = 4.7 \text{ k}\Omega$ | 6N139 | t_{PHL} | | 6.0 | 25 | μs |
| | $I_F = 12 \text{ mA}$, $R_L = 270 \Omega$ | 6N139 | t_{PHL} | | 0.6 | 1.0 | μs |
| Propagation delay time to logic high at output | $I_F = 1.6 \text{ mA}$, $R_L = 2.2 \text{ k}\Omega$ | 6N138 | t_{PLH} | | 2.0 | 35 | μs |
| | $I_F = 0.5 \text{ mA}$, $R_L = 4.7 \text{ k}\Omega$ | 6N139 | t_{PLH} | | 4.0 | 60 | μs |
| Propagation delay time to logic high at output ^{6), 8)} | $I_F = 12 \text{ mA}$, $R_L = 270 \Omega$ | 6N139 | t_{PLH} | | 1.5 | 7.0 | μs |

⁶⁾ Pin 7 open

⁸⁾ Using a resistor between pin 5 and 7 will decrease gain and delay time.

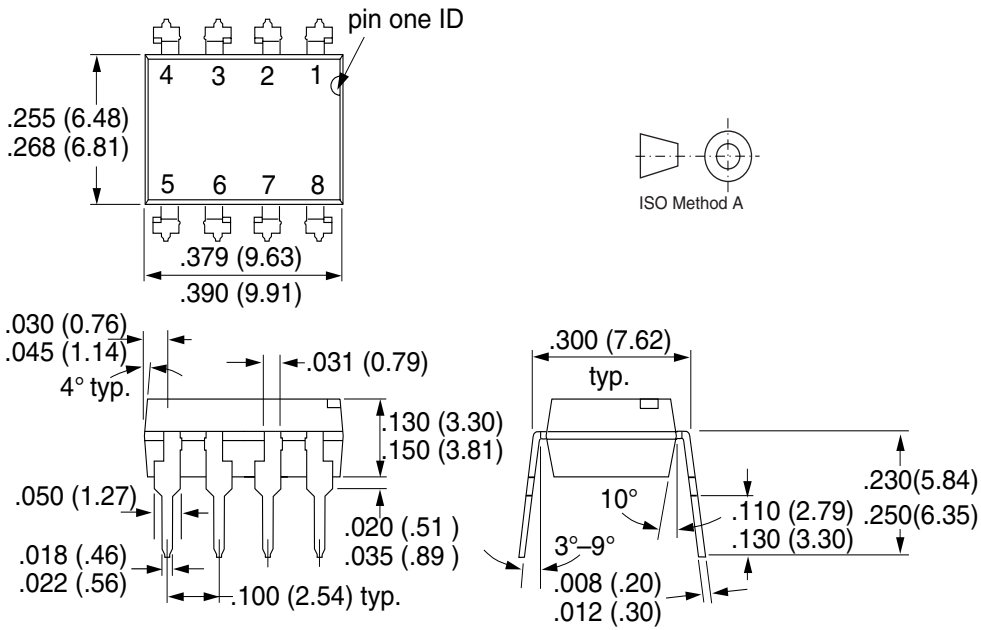
Common Mode Transient Immunity

| Parameter | Test condition | Symbol | Min | Typ. | Max | Unit |
|--|--|----------|-----|-------|-----|------------------------|
| Common mode transient immunity, logic high level output ^{9), 10)} | $I_F = 0 \text{ mA}$, $R_L = 2.2 \text{ k}\Omega$, $R_{CC} = 0$, $ V_{CM} = 10 \text{ V}_{P-P}$ | $ CM_H $ | | 500 | | $\text{V}/\mu\text{s}$ |
| Common mode transient immunity, logic low level output ^{9), 10)} | $I_F = 1.6 \text{ mA}$, $R_L = 2.2 \text{ k}\Omega$, $R_{CC} = 0$, $ V_{CM} = 10 \text{ V}_{P-P}$ | $ CM_L $ | | - 500 | | $\text{V}/\mu\text{s}$ |

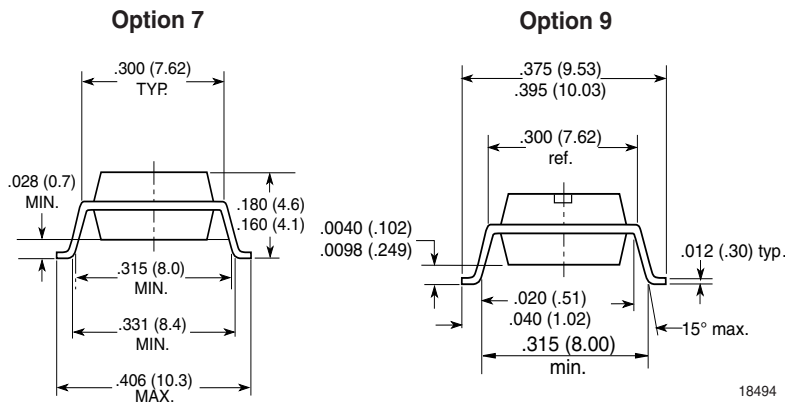
⁹⁾ Common mode transient immunity in logic high level is the maximum tolerable (positive) dV_{CM}/dt on the leading edge of the common mode pulse, V_{CM} , to assure that the output will remain in a logic high state (i.e. $V_O > 2.0 \text{ V}$) common mode transient immunity in logic low level is the maximum tolerable (negative) dV_{CM}/dt on the trailing edge of the common mode pulse signal, V_{CM} to assure that the output will remain in a logic low state (i.e. $V_O < 0.8 \text{ V}$).

¹⁰⁾ In applications where dv/dt may exceed $50,000 \text{ V}/\mu\text{s}$ (such as state discharge) a series resistor, R_{CC} should be included to protect I_C from destructively high surge currents. The recommend value is $R_{CC} \cong [(1 \text{ V}) / (0.15 I_F (\text{mA}))] \text{ K}\Omega$

Package Dimensions in Inches (mm)



i178006



18494

Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design
and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany
Telephone: 49 (0)7131 67 2831, Fax number: 49 (0)7131 67 2423